

AOS Semiconductor Product Reliability Report

A08830/A08830L, rev A

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AO8830/L. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO8830/Lpasses AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AO8830/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{GS(MAX)}$ rating. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration. AO8830 and AO8830L are electrically identical.

-RoHS Compliant -A08830L is Halogen Free

Parameter Drain-Source Voltage		Symbol	Maximum	Units	
		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	±12	V	
Continuous Drain	T _A =25°C		6		
Current ^A	T _A =70°C	ID	4.8	А	
Pulsed Drain Current ^B		I _{DM}	30	7	
	T _A =25°C	D	1.5	14/	
Power Dissipation ^A	T _A =70°C	PD	0.94	- w	
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

Thermal Characteristics					
Parameter	Symbol	Тур	Мах	Units	
Maximum Junction-to-Ambient ^A	t ≤ 10s	R _{eja}	64	83	°C/W
Maximum Junction-to-Ambient ^A	Steady-State	ATe	115	140	°C/W
Maximum Junction-to-Lead ^c	Steady-State	R _{ejl}	70	85	°C/W



II. Die / Package Information:

	AO8830	AO8830L (Green Compound)
Process	Standard sub-micron	Standard sub-micron
	Low voltage N channel process	low voltage N channel process
Package Type	TSSOP-8	TSSOP-8
Lead Frame	Cu, S/pad, Ag spot	Cu, S/pad, Ag spot
Die Attach	Ag epoxy	Ag epoxy
Bond wire	2 mils Au wire	2 mils Au wire
Mold Material	Epoxy resin with silica filler	Epoxy resin with silica filler
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1*

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO8830 (Standard) & AO8830L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°c Green: 168hr 85°c /85RH +3 cycle reflow@260°c	-	Standard: 11 lots Green: 4 lots	1705 pcs	0	
HTGB	Temp = 150°c, Vgs=100% of Vgsmax	168hrs 500 hrs 1000 hrs	2 lots (Note A*)	154 pcs 77 pcs / lot	0	
HTRB	Temp = 150°c , Vds=80% of Vdsmax	168hrs 500 hrs 1000 hrs	2 lots (Note A*)	154 pcs 77 pcs / lot	0	
HAST	130 +/- 2°c , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 6 lots Green: 4 lots (Note B**)	550 pcs 55 pcs / lot	0	
Pressure Pot 121°c , 29.7psi, RH=100%		96 hrs	Standard: 11 lots Green: 4 lots (Note B**)	825 pcs 55 pcs / lot	0	
Temperature Cycle	-65°c to 150°c , air to air,	250 / 500 cycles	Standard: 3 lots Green: 3 lots (Note B**)	330 pcs 55 pcs / lot	0	



III. Result of Reliability Stress for AO8830 (Standard) & AO8830L (Green) Continues

Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
	NA	5	5	0
Room Temp 150°c bake 150°c bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
245°c	5 sec	15	15 leads	0
	Cross-section X-ray Room Temp 150°c bake 150°c bake	Cross-section X-rayNARoom Temp 150°c bake 150°c bake0hr 250hr 500hr	Cross-section5X-ray5NA5Room Temp0hr150°c bake250hr150°c bake500hr	Cross-section X-ray55NA55Room Temp 150°c bake0hr40400 40 wires 250hr40400 40 wires 4040 wires 40 wires

Note A: The HTGB and HTRB reliability data presents total of available AO8830/L burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO8830/L comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion): 23 MTTF = 4957 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AOB414). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 \text{ (N) (H) (Af)}] = 1.83 \times 10^9 / [2x4x77x500x258] = 23$ MTTF = $10^9 / \text{FIT} = 4.34 \times 10^7 \text{hrs} = 4957 \text{ years}$

 Chi^2 = Chi Squared Distribution, determined by the number of failures and confidence interval N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55 $^{\circ}$ C) Acceleration Factor [**Af**] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:								
		55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
	Af	258	87	32	13	5.64	2.59	1

Tjs = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tju =The use junction temperature in degree (Kelvin), K = C+273.16

 \mathbf{k} = Boltzmann's constant, 8.617164 X 10⁻⁵ eV/K